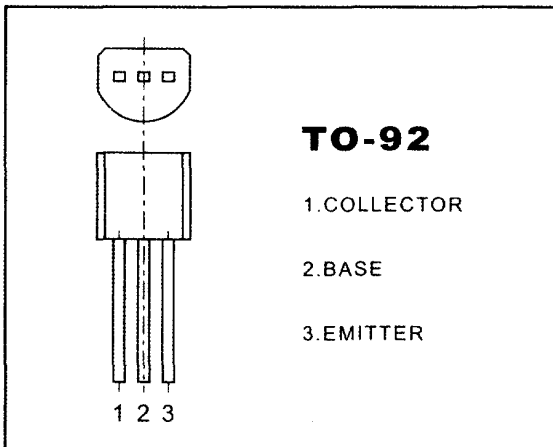


TO-92 Plastic-Encapsulate Transistors

BC184,B,C TRANSISTOR(NPN)



FEATURES

Power dissipation

P_{CM} : 0.35W ($T_{amb}=25^{\circ}C$)

Collector current

I_{CM} : 0.1 A

Collector-base voltage

$V_{(BR)CBO}$: 45V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

ELECTRICAL CHARACTERISTICS

($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Typical Values		
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = 10 \mu A, I_E = 0$	45		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 2 mA, I_B = 0$	30		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 100 \mu A, I_C = 0$	6		V
Collector cut-off current	I_{CBO}	$V_{CB} = 30 V, I_E = 0$		15	nA
Collector cut-off current	I_{CEO}	$V_{CE} = 30V, I_B = 0$		0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 4 V, I_C = 0$		15	nA
DC current gain	BC184	$V_{CE} = 5 V, I_C = 2 mA$	240	900	
	BC184B		240	500	
	BC184C		450	900	
Collector-emitter saturation voltage	V_{CEsat}	$I_C = 100 mA, I_B = 5 mA$		0.6	V
Base-emitter saturation voltage	V_{BEsat}	$I_C = 100 mA, I_B = 5 mA$		1.2	V
Transition frequency	f_T	$V_{CE} = 5 V, I_C = 10 mA$ $f = 100MHz$	150		MHz